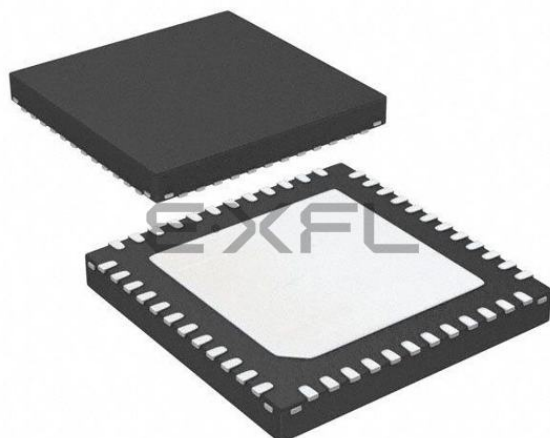




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-WFQFN Exposed Pad
Supplier Device Package	48-HWQFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104gcana-w0

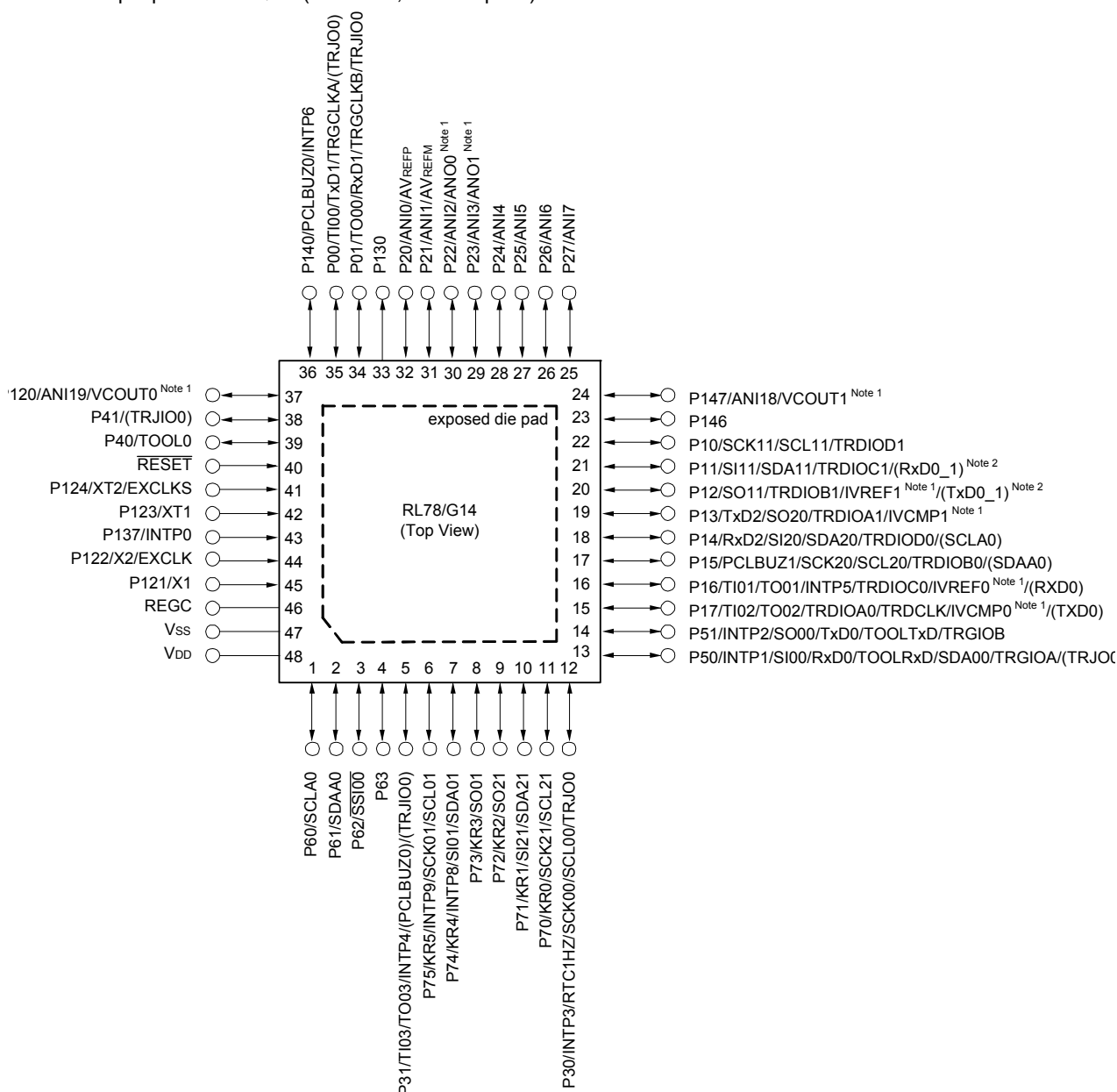
(1/5)

Pin count	Package	Fields of Application Note	Ordering Part Number
30 pins	30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)	A	R5F104AAASP#V0, R5F104ACASP#V0, R5F104ADASP#V0, R5F104AEASP#V0, R5F104AFASP#V0, R5F104AGASP#V0 R5F104AAASP#X0, R5F104ACASP#X0, R5F104ADASP#X0, R5F104AEASP#X0, R5F104AFASP#X0, R5F104AGASP#X0
		D	R5F104AADSP#V0, R5F104ACDSP#V0, R5F104ADDSP#V0, R5F104AEDSP#V0, R5F104AFDSP#V0, R5F104AGDSP#V0 R5F104AADSP#X0, R5F104ACDSP#X0, R5F104ADDSP#X0, R5F104AEDSP#X0, R5F104AFDSP#X0, R5F104AGDSP#X0
		G	R5F104AAGSP#V0, R5F104ACGSP#V0, R5F104ADGSP#V0, R5F104AEGSP#V0, R5F104AFGSP#V0, R5F104AGGSP#V0 R5F104AAGSP#X0, R5F104ACGSP#X0, R5F104ADGSP#X0, R5F104AEGSP#X0, R5F104AFGSP#X0, R5F104AGGSP#X0
32 pins	32-pin plastic HWQFN (5 × 5 mm, 0.5 mm pitch)	A	R5F104BAANA#U0, R5F104BCANA#U0, R5F104BDANA#U0, R5F104BEANA#U0, R5F104BFANA#U0, R5F104BGANA#U0 R5F104BAANA#W0, R5F104BCANA#W0, R5F104BDANA#W0, R5F104BEANA#W0, R5F104BFANA#W0, R5F104BGANA#W0
		D	R5F104BADNA#U0, R5F104BCDNA#U0, R5F104BDDNA#U0, R5F104BEDNA#U0, R5F104BFDNA#U0, R5F104BGDNA#U0 R5F104BADNA#W0, R5F104BCDNA#W0, R5F104BDDNA#W0, R5F104BEDNA#W0, R5F104BFDNA#W0, R5F104BGDNA#W0
		G	R5F104BAGNA#U0, R5F104BCGNA#U0, R5F104BDGNA#U0, R5F104BEGNA#U0, R5F104BFGNA#U0, R5F104BGGNA#U0 R5F104BAGNA#W0, R5F104BCGNA#W0, R5F104BDGNA#W0, R5F104BEGNA#W0, R5F104BFGNA#W0, R5F104BGGNA#W0
	32-pin plastic LQFP (7 × 7, 0.8 mm pitch)	A	R5F104BAAFP#V0, R5F104BCAFP#V0, R5F104BDAFP#V0, R5F104BEAFP#V0, R5F104BFAFP#V0, R5F104BGAFP#V0 R5F104BAAFP#X0, R5F104BCAFP#X0, R5F104BDAFP#X0, R5F104BEAFP#X0, R5F104BFAFP#X0, R5F104BGAFP#X0
		D	R5F104BADFP#V0, R5F104BCDFP#V0, R5F104BDDFP#V0, R5F104BEDFP#V0, R5F104BDFP#V0, R5F104BGDFP#V0 R5F104BADFP#X0, R5F104BCDFP#X0, R5F104BDDFP#X0, R5F104BEDFP#X0, R5F104BDFP#X0, R5F104BGDFP#X0
		G	R5F104BAGFP#V0, R5F104BCGFP#V0, R5F104BDGFP#V0, R5F104BEGFP#V0, R5F104BFGFP#V0, R5F104BGGFP#V0 R5F104BAGFP#X0, R5F104BCGFP#X0, R5F104BDGFP#X0, R5F104BEGFP#X0, R5F104BFGFP#X0, R5F104BGGFP#X0
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	A	R5F104CAALA#U0, R5F104CCALA#U0, R5F104CDALA#U0, R5F104CEALA#U0, R5F104CFALA#U0, R5F104CGALA#U0 R5F104CAALA#W0, R5F104CCALA#W0, R5F104CDALA#W0, R5F104CEALA#W0, R5F104CFALA#W0, R5F104CGALA#W0
		G	R5F104CAGLA#U0, R5F104CCGLA#U0, R5F104CDGLA#U0, R5F104CEGLA#U0, R5F104CFGLA#U0, R5F104CGGLA#U0 R5F104CAGLA#W0, R5F104CCGLA#W0, R5F104CDGLA#W0, R5F104CEGLA#W0, R5F104CFGLA#W0, R5F104CGGLA#W0

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



Note 1. Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

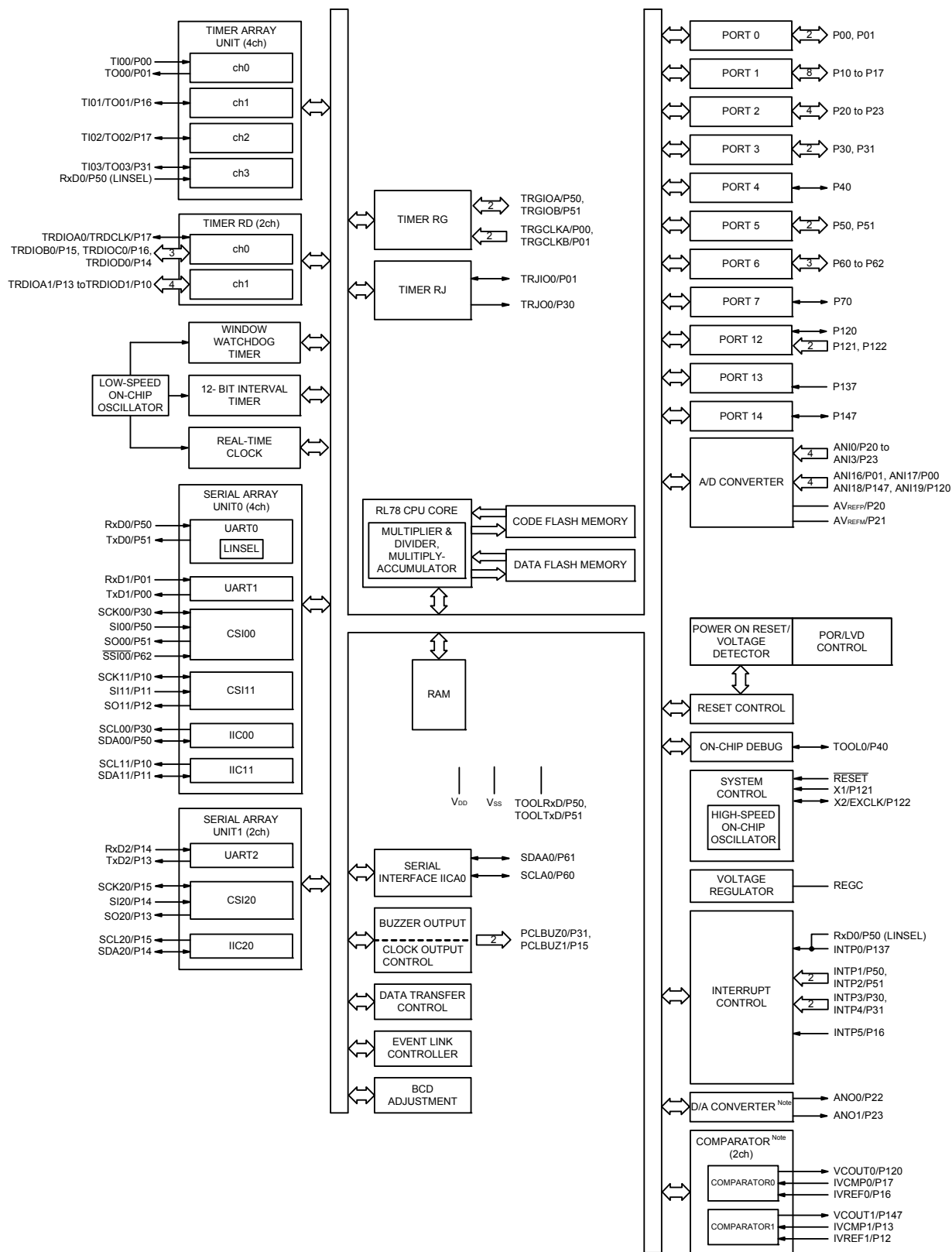
Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

Remark 3. It is recommended to connect an exposed die pad to Vss.

1.5.2 32-pin products



Note Mounted on the 96 KB or more code flash memory products.

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	f _{HOCO} = 64 MHz, f _{IIH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.6		mA
						V _{DD} = 3.0 V		2.6		
				f _{HOCO} = 32 MHz, f _{IIH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.3		
						V _{DD} = 3.0 V		2.3		
			HS (high-speed main) mode Note 5	f _{HOCO} = 64 MHz, f _{IIH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		5.4	10.2	mA
						V _{DD} = 3.0 V		5.4	10.2	
				f _{HOCO} = 32 MHz, f _{IIH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		5.0	9.6	
						V _{DD} = 3.0 V		5.0	9.6	
				f _{HOCO} = 48 MHz, f _{IIH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.2	7.8	
						V _{DD} = 3.0 V		4.2	7.8	
				f _{HOCO} = 24 MHz, f _{IIH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.0	7.4	
						V _{DD} = 3.0 V		4.0	7.4	
				f _{HOCO} = 16 MHz, f _{IIH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		3.0	5.3	
						V _{DD} = 3.0 V		3.0	5.3	
			LS (low-speed main) mode Note 5	f _{HOCO} = 8 MHz, f _{IIH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.4	2.3	mA
						V _{DD} = 2.0 V		1.4	2.3	
			LV (low-voltage main) mode Note 5	f _{HOCO} = 4 MHz, f _{IIH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.3	1.9	mA
						V _{DD} = 2.0 V		1.3	1.9	
			HS (high-speed main) mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.4	6.2	mA
						Resonator connection		3.6	6.4	
				f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.4	6.2	
						Resonator connection		3.6	6.4	
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.1	3.6	
						Resonator connection		2.2	3.7	
				f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.1	3.6	
						Resonator connection		2.2	3.7	
			LS (low-speed main) mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.2	2.2	mA
						Resonator connection		1.2	2.3	
				f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.2	2.2	
						Resonator connection		1.2	2.3	
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		4.9	7.1	μA
						Resonator connection		4.9	7.1	
				f _{SUB} = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		4.9	7.1	
						Resonator connection		4.9	7.1	
				f _{SUB} = 32.768 kHz Note 4 TA = +50°C	Normal operation	Square wave input		5.1	8.8	
						Resonator connection		5.1	8.8	
				f _{SUB} = 32.768 kHz Note 4 TA = +70°C	Normal operation	Square wave input		5.5	10.5	
						Resonator connection		5.5	10.5	
				f _{SUB} = 32.768 kHz Note 4 TA = +85°C	Normal operation	Square wave input		6.5	14.5	
						Resonator connection		6.5	14.5	

(Notes and Remarks are listed on the next page.)

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products**(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	HS (high-speed main) mode Note 5	f _{HOCO} = 64 MHz, f _{IIH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.9		mA
						V _{DD} = 3.0 V		2.9		
				f _{HOCO} = 32 MHz, f _{IIH} = 32 MHz Note 3	Basic operation	V _{DD} = 5.0 V		2.5		
						V _{DD} = 3.0 V		2.5		
			HS (high-speed main) mode Note 5	f _{HOCO} = 64 MHz, f _{IIH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		6.0	11.2	mA
						V _{DD} = 3.0 V		6.0	11.2	
				f _{HOCO} = 32 MHz, f _{IIH} = 32 MHz Note 3	Normal operation	V _{DD} = 5.0 V		5.5	10.6	
						V _{DD} = 3.0 V		5.5	10.6	
				f _{HOCO} = 48 MHz, f _{IIH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.7	8.6	
						V _{DD} = 3.0 V		4.7	8.6	
				f _{HOCO} = 24 MHz, f _{IIH} = 24 MHz Note 3	Normal operation	V _{DD} = 5.0 V		4.4	8.2	
						V _{DD} = 3.0 V		4.4	8.2	
				f _{HOCO} = 16 MHz, f _{IIH} = 16 MHz Note 3	Normal operation	V _{DD} = 5.0 V		3.3	5.9	
						V _{DD} = 3.0 V		3.3	5.9	
			LS (low-speed main) mode Note 5	f _{HOCO} = 8 MHz, f _{IIH} = 8 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.5	2.5	mA
						V _{DD} = 2.0 V		1.5	2.5	
			LV (low-voltage main) mode Note 5	f _{HOCO} = 4 MHz, f _{IIH} = 4 MHz Note 3	Normal operation	V _{DD} = 3.0 V		1.5	2.1	mA
						V _{DD} = 2.0 V		1.5	2.1	
			HS (high-speed main) mode Note 5	f _{MX} = 20 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		3.7	6.8	mA
						Resonator connection		3.9	7.0	
				f _{MX} = 20 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		3.7	6.8	
						Resonator connection		3.9	7.0	
				f _{MX} = 10 MHz Note 2, V _{DD} = 5.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
				f _{MX} = 10 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
			LS (low-speed main) mode Note 5	f _{MX} = 8 MHz Note 2, V _{DD} = 3.0 V	Normal operation	Square wave input		1.4	2.4	mA
						Resonator connection		1.4	2.5	
				f _{MX} = 8 MHz Note 2, V _{DD} = 2.0 V	Normal operation	Square wave input		1.4	2.4	
						Resonator connection		1.4	2.5	
			Subsystem clock operation	f _{SUB} = 32.768 kHz Note 4 TA = -40°C	Normal operation	Square wave input		5.2		μA
						Resonator connection		5.2		
				f _{SUB} = 32.768 kHz Note 4 TA = +25°C	Normal operation	Square wave input		5.3	7.7	
						Resonator connection		5.3	7.7	
				f _{SUB} = 32.768 kHz Note 4 TA = +50°C	Normal operation	Square wave input		5.5	10.6	
						Resonator connection		5.5	10.6	
				f _{SUB} = 32.768 kHz Note 4 TA = +70°C	Normal operation	Square wave input		5.9	13.2	
						Resonator connection		6.0	13.2	
				f _{SUB} = 32.768 kHz Note 4 TA = +85°C	Normal operation	Square wave input		6.8	17.5	
						Resonator connection		6.9	17.5	

(Notes and Remarks are listed on the next page.)

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products**(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)****(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit			
Supply current Note 1	IDD2 Note 2	HALT mode	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.93	3.32	mA			
					VDD = 3.0 V		0.93	3.32				
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.5	2.63				
					VDD = 3.0 V		0.5	2.63				
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.72	2.60				
					VDD = 3.0 V		0.72	2.60				
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.42	2.03				
					VDD = 3.0 V		0.42	2.03				
				fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.39	1.50				
					VDD = 3.0 V		0.39	1.50				
				LS (low-speed main) mode Note 7	fHOCO = 8 MHz, fIH = 8 MHz Note 4	VDD = 3.0 V		270		800	μA	
						VDD = 2.0 V		270		800		
				LV (low-voltage main) mode Note 7	fHOCO = 4 MHz, fIH = 4 MHz Note 4	VDD = 3.0 V		450		755	μA	
						VDD = 2.0 V		450		755		
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.31	1.69	mA			
						Resonator connection		0.41		1.91		
					Square wave input		0.31	1.69				
						Resonator connection		0.41		1.91		
					fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.21		0.94		
							Resonator connection			0.26	1.02	
					fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.21		0.94		
							Resonator connection			0.26	1.02	
					LS (low-speed main) mode Note 7	fMX = 8 MHz Note 3, VDD = 3.0 V	Square wave input			110	610	μA
							Resonator connection			150	660	
						fMX = 8 MHz Note 3, VDD = 2.0 V	Square wave input			110	610	
							Resonator connection			150	660	
					Subsystem clock operation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input			0.31		μA
							Resonator connection			0.50		
			fSUB = 32.768 kHz Note 5, TA = +25°C	Square wave input			0.38	0.76				
				Resonator connection			0.57	0.95				
			fSUB = 32.768 kHz Note 5, TA = +50°C	Square wave input			0.47	3.59				
				Resonator connection			0.70	3.78				
			fSUB = 32.768 kHz Note 5, TA = +70°C	Square wave input			0.80	6.20				
				Resonator connection			1.00	6.39				
			fSUB = 32.768 kHz Note 5, TA = +85°C	Square wave input			1.65	10.56				
				Resonator connection			1.84	10.75				
			IDD3 Note 6	STOP mode Note 8	TA = -40°C					0.19		μA
					TA = +25°C					0.30	0.59	
					TA = +50°C					0.41	3.42	
					TA = +70°C					0.80	6.03	
					TA = +85°C					1.53	10.39	

(Notes and Remarks are listed on the next page.)

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	tTDIH, tTDIL	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/fCLK			ns
Timer RD forced cutoff signal input low-level width	tTDSIL	P130/INTP0	2MHz < fCLK ≤ 32 MHz	1			μs
			fCLK ≤ 2 MHz	1/fCLK + 1			
Timer RG input high-level width, low-level width	tTGIH, tTGIL	TRGIOA, TRGIOB		2.5/fCLK			ns
TO00 to TO03, TO10 to TO13, TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	fTO	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.6 V ≤ EVDD0 ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	fPCL	HS (high-speed main) mode	4.0 V ≤ EVDD0 ≤ 5.5 V			16	MHz
			2.7 V ≤ EVDD0 < 4.0 V			8	MHz
			1.8 V ≤ EVDD0 < 2.7 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EVDD0 ≤ 5.5 V			4	MHz
			1.6 V ≤ EVDD0 < 1.8 V			2	MHz
Interrupt input high-level width, low-level width	tINTH, tINTL	INTP0	1.6 V ≤ VDD ≤ 5.5 V	1			μs
		INTP1 to INTP11	1.6 V ≤ EVDD0 ≤ 5.5 V	1			μs
Key interrupt input low-level width	tKR	KR0 to KR7	1.8 V ≤ EVDD0 ≤ 5.5 V	250			ns
			1.6 V ≤ EVDD0 < 1.8 V	1			μs
RESET low-level width	tRSL			10			μs

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)**(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)**

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t _{KCY1}	t _{KCY1} ≥ 4/f _{CLK}	2.7 V ≤ EVDD0 ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EVDD0 ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EVDD0 ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EVDD0 ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EVDD0 ≤ 5.5 V	—		1000		1000		ns
SCKp high-/low-level width	t _{KH1} , t _{KL1}	4.0 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 12		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 18		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 38		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		t _{KCY1} /2 - 50		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		t _{KCY1} /2 - 100		t _{KCY1} /2 - 100		t _{KCY1} /2 - 100		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		t _{KCY1} /2 - 100		t _{KCY1} /2 - 100		ns
Slp setup time (to SCKp↑) Note 1	t _{SIK1}	4.0 V ≤ EVDD0 ≤ 5.5 V		44		110		110		ns
		2.7 V ≤ EVDD0 ≤ 5.5 V		44		110		110		ns
		2.4 V ≤ EVDD0 ≤ 5.5 V		75		110		110		ns
		1.8 V ≤ EVDD0 ≤ 5.5 V		110		110		110		ns
		1.7 V ≤ EVDD0 ≤ 5.5 V		220		220		220		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		220		220		ns
Slp hold time (from SCKp↑) Note 2	t _{KSI1}	1.7 V ≤ EVDD0 ≤ 5.5 V		19		19		19		ns
		1.6 V ≤ EVDD0 ≤ 5.5 V		—		19		19		ns
Delay time from SCKp↓ to SOp output Note 3	t _{KSO1}	1.7 V ≤ EVDD0 ≤ 5.5 V C = 30 pF Note 4			25		25		25	ns
		1.6 V ≤ EVDD0 ≤ 5.5 V C = 30 pF Note 4			—		25		25	ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes “to SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes “from SCKp↓” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes “from SCKp↑” when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Note 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the Slp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

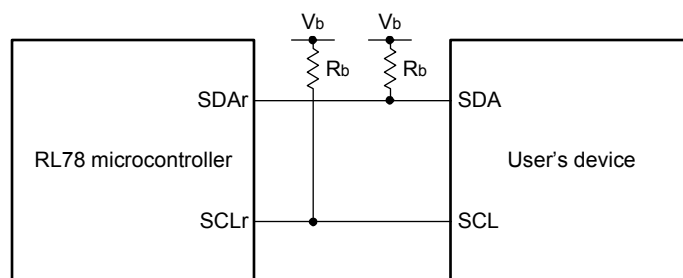
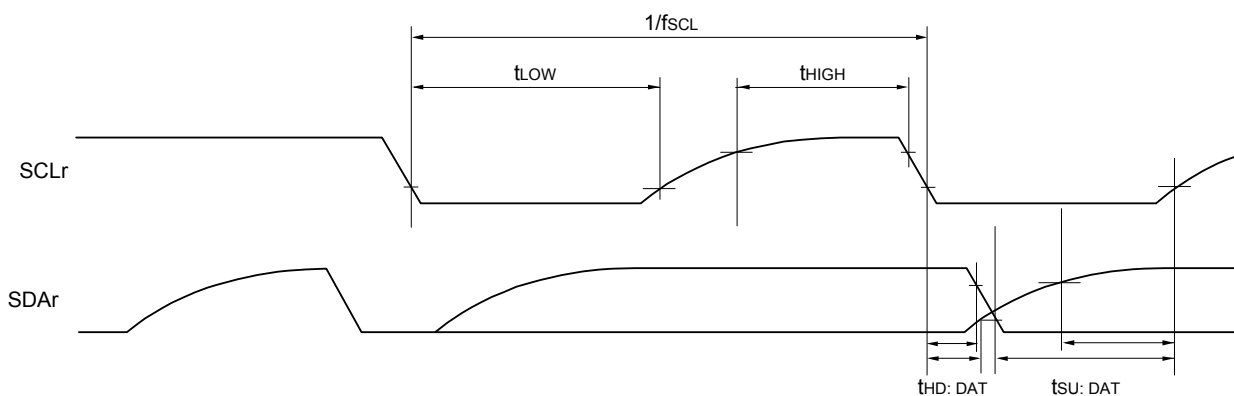
(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)**(TA = -40 to +85°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)****(2/2)**

Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:DAT	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 50 pF, Rb = 2.7 kΩ	1/fMCK + 135 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 50 pF, Rb = 2.7 kΩ	1/fMCK + 135 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
		4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 100 pF, Rb = 2.8 kΩ	1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 100 pF, Rb = 2.7 kΩ	1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V Note 2, Cb = 100 pF, Rb = 5.5 kΩ	1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		1/fMCK + 190 Note 3		ns
Data hold time (transmission)	tHD:DAT	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 50 pF, Rb = 2.7 kΩ	0	305	0	305	0	305	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 50 pF, Rb = 2.7 kΩ	0	305	0	305	0	305	ns
		4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 100 pF, Rb = 2.8 kΩ	0	355	0	355	0	355	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 100 pF, Rb = 2.7 kΩ	0	355	0	355	0	355	ns
		1.8 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V Note 2, Cb = 100 pF, Rb = 5.5 kΩ	0	405	0	405	0	405	ns

Note 1. The value must also be equal to or less than fMCK/4.**Note 2.** Use it with EVDD0 ≥ Vb.**Note 3.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

Remark 1. $R_b[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage

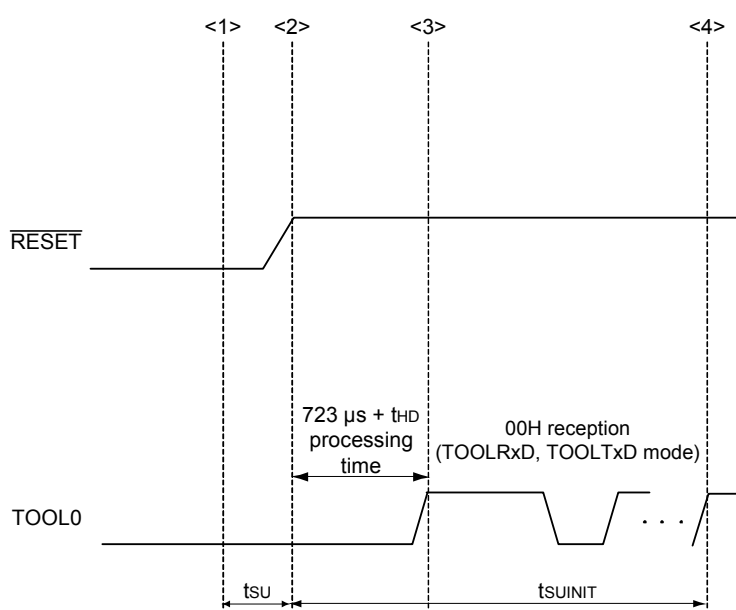
Remark 2. r : IIC number ($r = 00, 01, 10, 11, 20, 30, 31$), g : PIM, POM number ($g = 0, 1, 3$ to $5, 14$)

Remark 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m : Unit number ($m = 0, 1$),
 n : Channel number ($n = 0, 2$), $mn = 00, 01, 02, 10, 12, 13$)

2.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +85°C, 1.8 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified	tsuINIT	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory)	tHD	POR and LVD reset must end before the external reset ends.	1			ms



<1> The low level is input to the TOOL0 pin.

<2> The external reset ends (POR and LVD reset must end before the external reset ends).

<3> The TOOL0 pin is set to the high level.

<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuINIT: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends

tHD: How long to keep the TOOL0 pin at the low level from when the external resets end (excluding the processing time of the firmware to control the flash memory)

- Note 1.** Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or VSS, EVSS0, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** During HALT instruction execution by flash memory.
- Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4.** When high-speed system clock and subsystem clock are stopped.
- Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6.** Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: $2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }32\text{ MHz}$
 $2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}@1\text{ MHz to }16\text{ MHz}$
- Note 8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1.** fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** fIH: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** fSUB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

<R>

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products**($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)****(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit	
Supply current Note 1	IDD2 Note 2	HALT mode	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.93	5.16	mA	
					VDD = 3.0 V		0.93	5.16		
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.5	4.47		
					VDD = 3.0 V		0.5	4.47		
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.72	4.08		
					VDD = 3.0 V		0.72	4.08		
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.42	3.51		
					VDD = 3.0 V		0.42	3.51		
				fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.39	2.38		
					VDD = 3.0 V		0.39	2.38		
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.31	2.83	mA	
					Resonator connection		0.41	2.92		
				fMX = 20 MHz Note 3, VDD = 3.0 V	Square wave input		0.31	2.83		
					Resonator connection		0.41	2.92		
				fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.21	1.46		
					Resonator connection		0.26	1.57		
				fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.21	1.46		
					Resonator connection		0.26	1.57		
		Subsystem clock operation	fsUB = 32.768 kHz Note 5, TA = -40°C	Square wave input		0.31	0.76	μA		
				Resonator connection		0.50	0.95			
				fsUB = 32.768 kHz Note 5, TA = +25°C	Square wave input		0.38		0.76	
					Resonator connection		0.57		0.95	
				fsUB = 32.768 kHz Note 5, TA = +50°C	Square wave input		0.47		3.59	
					Resonator connection		0.70		3.78	
				fsUB = 32.768 kHz Note 5, TA = +70°C	Square wave input		0.80		6.20	
					Resonator connection		1.00		6.39	
				fsUB = 32.768 kHz Note 5, TA = +85°C	Square wave input		1.65		10.56	
					Resonator connection		1.84		10.75	
				fsUB = 32.768 kHz Note 5, TA = +105°C	Square wave input		8.00		65.7	
					Resonator connection		8.00		65.7	
	IDD3 Note 6	STOP mode Note 8	TA = -40°C					0.19	0.63	μA
			TA = +25°C					0.30	0.63	
			TA = +50°C					0.41	3.47	
			TA = +70°C					0.80	6.08	
			TA = +85°C					1.53	10.44	
			TA = +105°C					6.50	67.14	

(Notes and Remarks are listed on the next page.)

- (3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = EV_{SS0} = EV_{SS1} = 0\text{ V}$, Reference voltage (+) = V_{DD} , Reference voltage (-) = V_{SS})

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$		1.2	± 7.0	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI0 to ANI14, ANI16 to ANI20	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
		10-bit resolution Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375		39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625		39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17		39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$			± 2.0	LSB
Analog input voltage	V_{AIN}	ANI0 to ANI14		0		V_{DD}	V
		ANI16 to ANI20		0		EV_{DD0}	V
		Internal reference voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{BGR} Note 3			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)		V_{TMPS25} Note 3			V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(2) Interrupt & Reset Mode**($T_A = -40$ to $+105^\circ\text{C}$, $V_{PDR} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Voltage detection threshold	VLVDD0	VPOC2, VPOC1, VPOC0 = 0, 1, 1, falling reset voltage		2.64	2.75	2.86	V
	VLVDD1	LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3	LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

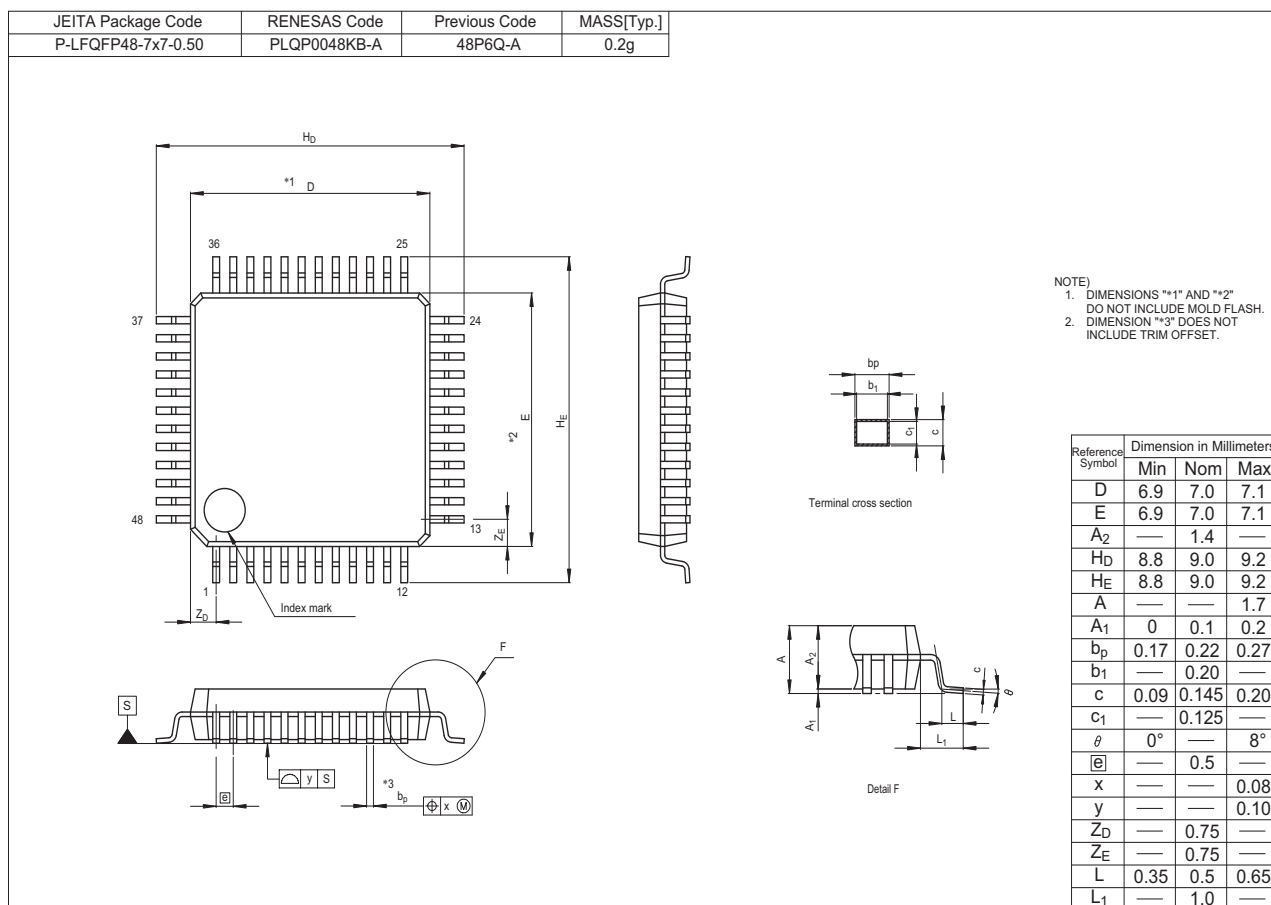
3.6.7 Power supply voltage rising slope characteristics**($T_A = -40$ to $+105^\circ\text{C}$, $V_{SS} = 0\text{ V}$)**

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

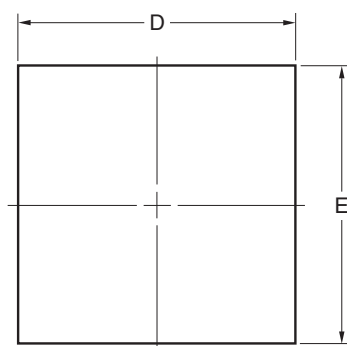
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R5F104GKGFB, R5F104GLGFB

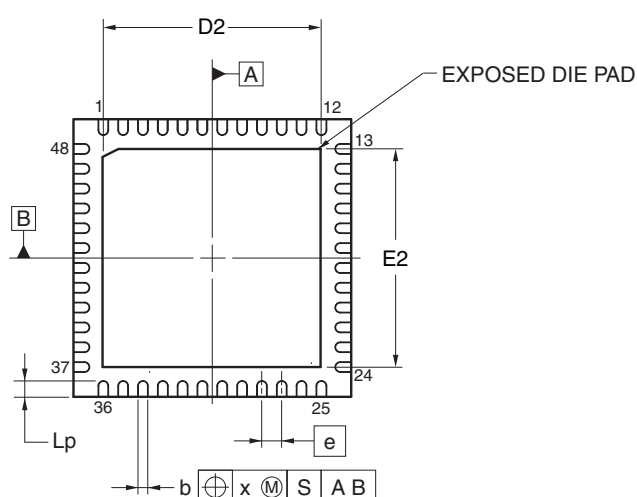
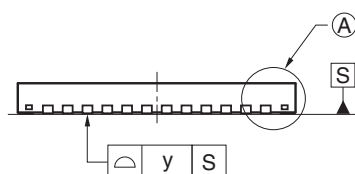
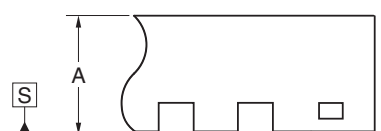


R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA,
 R5F104GHANA, R5F104GJANA
 R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA,
 R5F104GHDNA, R5F104GJDNA
 R5F104GAGNA, R5F104GCGNA, R5F104GDGNA, R5F104GEGNA, R5F104GFGNA, R5F104GGGNA,
 R5F104GHGNA, R5F104GJGNA
 R5F104GKANA, R5F104GLANA
 R5F104GKGNA, R5F104GLGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-5	0.13



DETAIL OF (A) PART

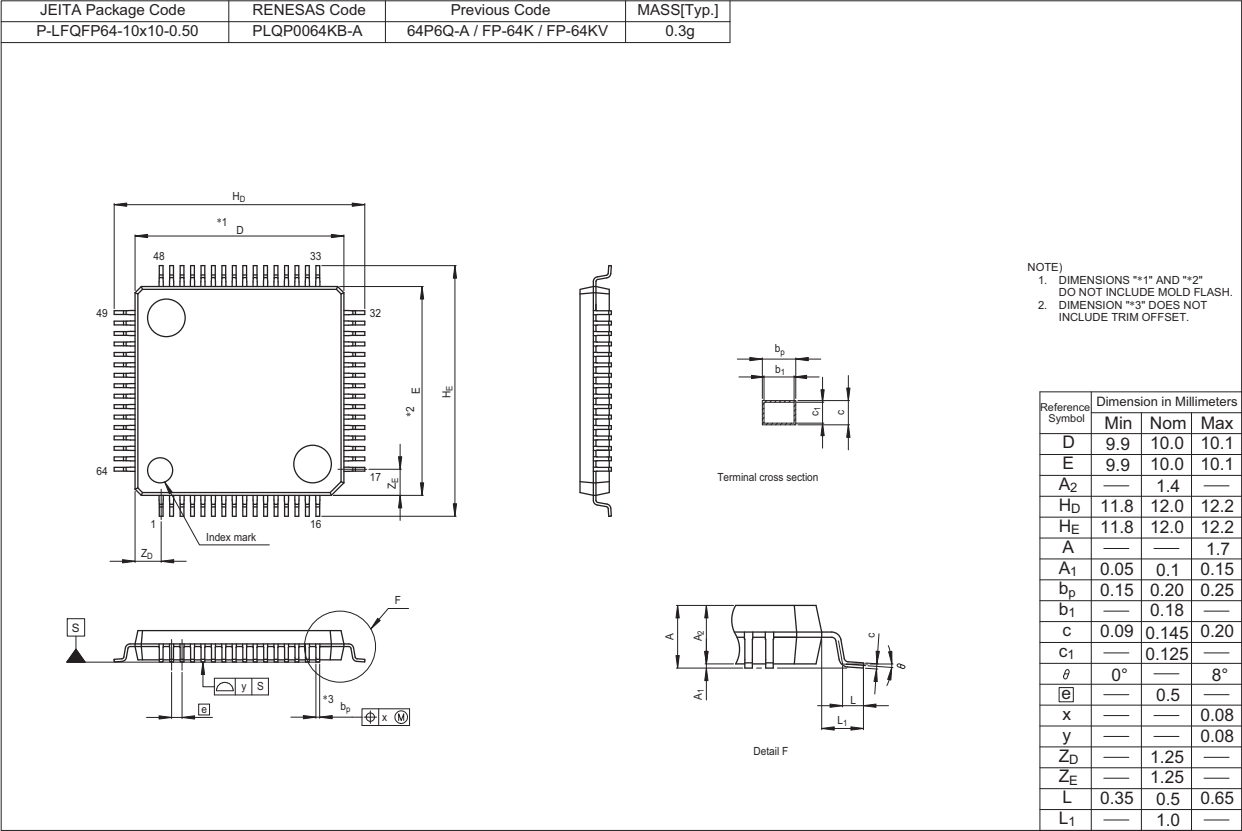


Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.95	7.00	7.05
E	6.95	7.00	7.05
A	0.70	0.75	0.80
b	0.18	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	A	5.45	5.50	5.55	5.45	5.50	5.55

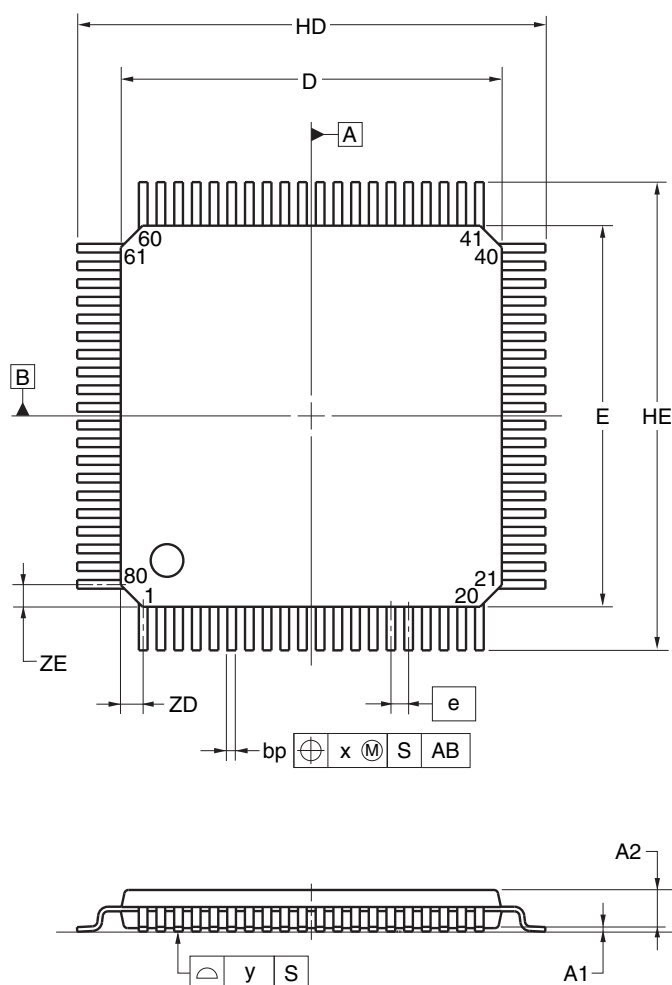
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R5F104LKAFB, R5F104LLAFB
R5F104LKGFB, R5F104LLGFB

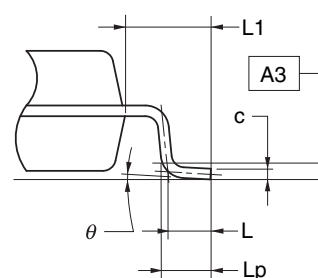


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 R5F104MFDFA, R5F104MGDFA, R5F104MHDFA, R5F104MJDFA
 R5F104MFGFA, R5F104MGGFA, R5F104MHGFA, R5F104MJGFA
 R5F104MKAFA, R5F104MLAFA
 R5F104MKGFA, R5F104MLGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



detail of lead end



Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	13.80	14.00	14.20
E	13.80	14.00	14.20
HD	17.00	17.20	17.40
HE	17.00	17.20	17.40
A	—	—	1.70
A1	0.05	0.125	0.20
A2	1.35	1.40	1.45
A3	—	0.25	—
bp	0.26	0.32	0.38
c	0.10	0.145	0.20
L	—	0.80	—
Lp	0.736	0.886	1.036
L1	1.40	1.60	1.80
θ	0°	3°	8°
e	—	0.65	—
x	—	—	0.13
y	—	—	0.10
ZD	—	0.825	—
ZE	—	0.825	—

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REVISION HISTORY	RL78/G14 Datasheet
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Rev.	Date	Description	
		Page	Summary
2.00	Oct 25, 2013	112 to 169 171 to 187	Addition of CHAPTER 3 ELECTRICAL SPECIFICATIONS Modification of 4.1 30-pin products to 4.10 100-pin products
3.00	Feb 07, 2014	All 1 2 3 6 to 8 15, 16 17 18, 19 20 21, 22 35, 37, 39, 41, 43, 45, 47 42, 43 46, 47 65 to 68 118 137 to 140 180 189, 190 191 193 to 195 198, 199 201, 202	Addition of products with maximum 512 KB flash ROM and 48 KB RAM Modification of 1.1 Features Modification of ROM, RAM capacities and addition of note 3 Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14 Addition of part number Modification of 1.3.6 48-pin products Modification of 1.3.7 52-pin products Modification of 1.3.8 64-pin products Modification of 1.3.9 80-pin products Modification of 1.3.10 100-pin products Modification of operating ambient temperature in 1.6 Outline of Functions Addition of table of 48-pin, 52-pin, 64-pin products (code flash memory 384 KB to 512 KB) Addition of table of 80-pin, 100-pin products (code flash memory 384 KB to 512 KB) Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products Modification of 2.7 Data Memory Retention Characteristics Addition of (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products Modification of 3.7 Data Memory Retention Characteristics Addition and modification of 4.6 48-pin products Modification of 4.7 52-pin products Addition and modification of 4.8 64-pin products Addition and modification of 4.9 80-pin products Addition and modification of 4.10 100-pin products
3.20	Jan 05, 2015	p.2 p.6 p.6 to 8 p.17 p.36, 39, 42, 45, 48, 50, 52 p.46, 48 p.47 p.62, 64, 66, 68, 70, 72	Deletion of R5F104JK and R5F104JL from the list of ROM and RAM capacities and modification of note Deletion of ordering part numbers of R5F104JK and R5F104JL from 52-pin plastic LQFP package in 1.2 Ordering Information Deletion of note 2 in 1.2 Ordering Information Deletion of note 2 in 1.3.7 52-pin products Modification of description in 1.6 Outline of Functions Deletion of description of 52-pin in 1.6 Outline of Functions Modification of note of 1.6 Outline of Functions Modification of specifications in 2.3.2 Supply current characteristics